Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	1347	(438/14).CCLS.	USPAT; USOCR	OR	OFF	2005/08/30 09:47
S2	814	S1 and (wafer with (semiconductor or conductor))	US-PGPUB; USPAT	OR	ON	2005/08/30 09:48
S3	98	S2 and "insulator"	US-PGPUB; USPAT	OR	ON	2005/08/30 09:49
S4	1	S2 and "insulator" with region with "locally thin"	US-PGPUB; USPAT	OR	ON	2005/08/30 09:50
S5	1	S2 and (region with "locally thin")	US-PGPUB; USPAT	OR	ON	2005/08/30 09:50
S6	1	S1 and (insulator with "locally thin")	US-PGPUB; USPAT	OR	ON	2005/08/30 09:51
S7	6	S1 and "locally thin"	US-PGPUB; USPAT	OR	ON	2005/08/30 09:54
S8	0	"locally thin insulator"	US-PGPUB; USPAT	OR	ON	2005/08/30 09:54
S9	1420	"thin insulator"	US-PGPUB; USPAT	OR	ON	2005/08/30 09:54
S10	229	S9 and (wafer with (semiconductor or conductor))	US-PGPUB; USPAT	OR	ON	2005/08/30 10:04
S11	810	((semiconductor or conductor) with insulator with "second conductor")	US-PGPUB; USPAT	OR	ON	2005/08/30 10:05
S12	2	S11 with "locally thin"	US-PGPUB; USPAT	OR	ON	2005/08/30 10:06
S13	2	S11 and "locally thin"	US-PGPUB; USPAT	OR	ON	2005/08/30 10:07
S14	2	S11 and ("locally thin" with (silicon oxide film or SiO2))	US-PGPUB; USPAT	OR	ON	2005/08/30 10:08
S15	292	S11 and (thin with (silicon oxide film or SiO2))	US-PGPUB; USPAT	OR	ON	2005/08/30 10:08
S16	525	S11 and (thin region with (silicon oxide film or SiO2))	US-PGPUB; USPAT	OR	ON	2005/08/30 10:11
S17	2	S11 and ("thin region" with (silicon oxide film or SiO2))	US-PGPUB; USPAT	OR	ON	2005/08/30 10:11
S18	4	S11 and ("thin region")	US-PGPUB; USPAT	OR	ON	2005/08/30 11:12
S19	1	("4697330").PN.	USPAT; USOCR	OR	OFF	2005/08/30 11:53
S20	0	"plasma etching" with "solid angle"	US-PGPUB; USPAT	OR	ON	2005/08/30 11:54
S21	103	(plasma with "solid angle")	US-PGPUB; USPAT	OR	ON	2005/12/15 12:17
S22	6972	"solid angle"	US-PGPUB; USPAT	OR	ON	2005/08/30 13:47

S23	0	S22 and (conductor with "insulator on second conductor")	US-PGPUB; USPAT	OR	ON	2005/08/30 13:48
S24	0	S22 and (conductor with "insulator on conductor")	US-PGPUB; USPAT	OR	ON	2005/08/30 13:48
S25	82	S22 and (conductor with insulator)	US-PGPUB; USPAT	OR	ON	2005/08/30 14:04
S26	2	S25 and ("this region" or "locally thin")	US-PGPUB; USPAT	OR	ON	2005/08/30 13:50
S27	0	S25 and ("this region")	US-PGPUB; USPAT	OR	ON	2005/08/30 13:50
S28	3	S25 and ("thin region")	US-PGPUB; USPAT	OR	ON	2005/08/30 13:50
S29	3	S25 and ("thin region" or "locally thin")	US-PGPUB; USPAT	OR	ON	2005/08/30 13:50
S30	19	S22 and "thin region"	US-PGPUB; USPAT	OR	ON	2005/08/30 14:06
S31	0	S22 and "silicon nitride film" with "thin region"	US-PGPUB; USPAT	OR	ON	2005/08/30 14:13
S32	8	S22 and thin with "silicon nitride film"	US-PGPUB; USPAT	OR	ON	2005/08/30 14:24
S33	19	S22 and thin adj1 region	US-PGPUB; USPAT	OR	ON	2005/08/30 14:25
S34	49	measuring same "ion current density"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/12/13 12:29
S37	25	"first region" with (ion and electron) with "second region"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/12/13 12:35
S38	7	(ion and electron) with launched	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/12/13 12:36
S39	281423	wafer	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/12/13 12:36
S40	7181	S39 and ((first or second) adj region)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/12/13 12:37

S41	4780	S40 and (ion or electron)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/12/13 12:37
S42	1782	S41 and plasma	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/12/13 12:37
S43	2	S42 and (measuring with "ion current density")	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/12/13 12:38
S44	10	S42 and "ion current density"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/12/13 12:38
S45	1041	"ion current density"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/12/13 14:13
S46	17	S45 and "measuring method"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/12/13 14:16
S47	71	S45 and (measuring with method)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/12/13 14:16
S48	26	S47 and electrons	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/12/13 14:16
S49	4	("5840199" | "5850042" | "5969393" | "6127255").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/12/13 14:22
S50	24994	wafer same plasma	US-PGPUB; USPAT; USOCR	OR	OFF	2005/12/14 13:29
S51	1604	S50 and (ion same electrons)	US-PGPUB; USPAT; USOCR	OR	OFF	2005/12/13 15:31

S52	107	S51 and "ion current density"	US-PGPUB; USPAT; USOCR	OR	OFF	2005/12/13 14:23
S53	18	S52 and measure	US-PGPUB; USPAT; USOCR	OR	OFF	2005/12/13 14:23
S54	24332	(ion same electrons)	US-PGPUB; USPAT; USOCR	OR	OFF	2005/12/13 15:32
S55	1198	S54 and "plasma etching"	US-PGPUB; USPAT; USOCR	OR	OFF	2005/12/13 15:32
S56	83	S55 and "ion current density"	US-PGPUB; USPAT; USOCR	OR	OFF	2005/12/13 15:32
S57	4	("2002/0123229").URPN.	USPAT	OR	OFF	2005/12/14 11:42
S58	1041	"ion current density"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/12/14 12:38
S59	71	S58 and (measuring with method)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/12/14 12:40
S60	4	S59 and criterion	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/12/14 12:41
S61	220	S58 and wafer same plasma	US-PGPUB; USPAT; USOCR	OR	OFF	2005/12/14 13:47
S62	4	S61 and criterion	US-PGPUB; USPAT; USOCR	OR	OFF	2005/12/14 13:29
S63	138	S61 and (ion same electron)	US-PGPUB; USPAT; USOCR	OR	OFF	2005/12/15 12:39
S64	5	(("4585516") or ("5298112") or ("5625526") or ("5593539") or ("5779925")).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/12/14 14:03
S65	3	"measured ion current density"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/12/14 14:46

S66	142	(measured same "ion current density")	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/12/14 14:47
S67	8	S66 and (manufacturing same based)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/12/14 14:47
S68	1	"device based" same "ion current density"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/12/14 15:04
S69	51	" based" same "ion current density"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/12/14 15:06
S70	0	" manufactured based" same "ion current density"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/12/14 15:06
S71	0	" manufactured based" with "ion current density"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/12/14 15:07
S72	0	S58 and "manufactured based"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/12/14 15:07
S73	26	("5102687" | "5474648").PN. OR ("5779925").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/12/15 12:00
S74	31	(conductor with "solid angle")	US-PGPUB; USPAT	OR	ON	2005/12/15 12:21
S75	7234	("solid angle")	US-PGPUB; USPAT	OR	ON	2005/12/15 12:22
S76	1067	S75 and ((2nd or second) with region)	US-PGPUB; USPAT	OR	ON	2005/12/15 12:35
S77	831	S76 and ((1st or first) with region)	US-PGPUB; USPAT	OR	ON	2005/12/15 12:36
S78	148	S77 and conductor	US-PGPUB; USPAT	OR	ON	2005/12/15 12:24
S79	124	S75 and ("2nd region" or "second region")	US-PGPUB; USPAT	OR	ON	2005/12/15 12:36

S80	103	S79 and ("1st region" or "first region")	US-PGPUB; USPAT	OR	ON	2005/12/15 12:36
S81	1041	"ion current density"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/12/15 12:39
S82	220	S81 and wafer same plasma	US-PGPUB; USPAT; USOCR	OR	OFF	2005/12/15 12:39
S83	138	S82 and (ion same electron)	US-PGPUB; USPAT; USOCR	OR	OFF	2005/12/15 12:39
S84	2	S83 and "solid angle"	US-PGPUB; USPAT; USOCR	OR	OFF	2005/12/15 12:39